

Mosfet Modeling For Vlsi Simulation Theory And Practice

This book constitutes the thoroughly refereed post-conference proceedings of the 7th International Conference on Numerical Methods and Applications, NMA 2010, held in Borovets, Bulgaria, in August 2010. The 60 revised full papers presented together with 3 invited papers were carefully reviewed and selected from numerous submissions for inclusion in this book. The papers are organized in topical sections on Monte Carlo and quasi-Monte Carlo methods, environmental modeling, grid computing and applications, metaheuristics for optimization problems, and modeling and simulation of electrochemical processes.

This volume compiles the papers presented at the conference which cover the various facets of semiconductor research with emphasis on microelectronics, VLSI and special aspects related to semiconductor applications. There are four sections: Microelectronics; Materials; Photovoltaics; and Gallium Arsenide Devices.

CMOS technology has now reached a state of evolution, in terms of both frequency and noise, where it is becoming a serious contender for radio frequency (RF) applications in the GHz range. Cutoff frequencies of about 50 GHz have been reported for 0.18 μm CMOS technology, and are expected to reach about 100 GHz when the feature size shrinks to 100 nm within a few years. This translates into CMOS circuit operating frequencies well into the GHz range, which covers the frequency range of many of today's popular wireless products, such as cell phones, GPS (Global Positioning System) and Bluetooth. Of course, the great interest in RF CMOS comes from the obvious advantages of CMOS technology in terms of production cost, high-level integration, and the ability to combine digital, analog and RF circuits on the same chip. This book discusses many of the challenges facing the CMOS RF circuit designer in terms of device modeling and characterization, which are crucial issues in circuit simulation and design.

Demand for on-site and alternative power generation is growing, fueled by government and public pressure to increase generation from renewable sources and energy efficient plant, and by the potential economic benefits resulting from privatization and deregulation of the supply sector. This book is a practical, course-derived guide that covers all aspects of embedded (or dispersed) generation, from prime mover characteristics to network reliability modelling. Topics include power quality, protection, reliability and economics. It is essential reading for practicing engineers responsible for planning, designing or specifying embedded generation solutions.

An expert guide to understanding and making optimum use of BSIM Used by more chip designers worldwide than any other comparable model, the Berkeley Short-Channel IGFET Model (BSIM) has, over the past few years, established itself as the de facto standard MOSFET SPICE model for circuit simulation and CMOS technology development. Yet,

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until now, there have been no independent expert guides or tutorials to supplement the various BSIM manuals currently available. Written by a noted expert in the field, this book fills that gap in the literature by providing a comprehensive guide to understanding and making optimal use of BSIM3 and BSIM4. Drawing upon his extensive experience designing with BSIM, William Liu provides a brief history of the model, discusses the various advantages of BSIM over other models, and explores the reasons why BSIM3 has been adopted by the majority of circuit manufacturers. He then provides engineers with the detailed practical information and guidance they need to master all of BSIM's features. He:

- Summarizes key BSIM3 components
- Represents the BSIM3 model with equivalent circuits for various operating conditions
- Provides a comprehensive glossary of modeling terminology
- Lists alphabetically BSIM3 parameters along with their meanings and relevant equations
- Explores BSIM3's flaws and provides improvement suggestions
- Describes all of BSIM4's improvements and new features
- Provides useful SPICE files, which are available online at the Wiley ftp site

Circuit simulation is essential in integrated circuit design, and the accuracy of circuit simulation depends on the accuracy of the transistor model. BSIM3v3 (BSIM for Berkeley Short-channel IGFET Model) has been selected as the first MOSFET model for standardization by the Compact Model Council, a consortium of leading companies in semiconductor and design tools. In the next few years, many fabless and integrated semiconductor companies are expected to switch from dozens of other MOSFET models to BSIM3. This will require many device engineers and most circuit designers to learn the basics of BSIM3. MOSFET Modeling & BSIM3 User's Guide explains the detailed physical effects that are important in modeling MOSFETs, and presents the derivations of compact model expressions so that users can understand the physical meaning of the model equations and parameters. It is the first book devoted to BSIM3. It treats the BSIM3 model in detail as used in digital, analog and RF circuit design. It covers the complete set of models, i.e., I-V model, capacitance model, noise model, parasitics model, substrate current model, temperature effect model and non quasi-static model. MOSFET Modeling & BSIM3 User's Guide not only addresses the device modeling issues but also provides a user's guide to the device or circuit design engineers who use the BSIM3 model in digital/analog circuit design, RF modeling, statistical modeling, and technology prediction. This book is written for circuit designers and device engineers, as well as device scientists worldwide. It is also suitable as a reference for graduate courses and courses in circuit design or device modelling. Furthermore, it can be used as a textbook for industry courses devoted to BSIM3. MOSFET Modeling & BSIM3 User's Guide is comprehensive and practical. It is balanced between the background information and advanced discussion of BSIM3. It is helpful to experts and students alike.

MOSFET Models for VLSI Circuit Simulation Theory and Practice Springer Science & Business Media

The editors and authors present a wealth of knowledge regarding the most relevant aspects in the field of MOS transistor

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modeling. The variety of subjects and the high quality of content of this volume make it a reference document for researchers and users of MOSFET devices and models. The book can be recommended to everyone who is involved in compact model developments, numerical TCAD modeling, parameter extraction, space-level simulation or model standardization. The book will appeal equally to PhD students who want to understand the ins and outs of MOSFETs as well as to modeling designers working in the analog and high-frequency areas.

During the first decade following the invention of the transistor, progress in semiconductor device technology advanced rapidly due to an effective synergy of technological discoveries and physical understanding. Through physical reasoning, a feeling for the right assumption and the correct interpretation of experimental findings, a small group of pioneers conceived the major analytic design equations, which are currently to be found in numerous textbooks. Naturally with the growth of specific applications, the description of some characteristic properties became more complicated. For instance, in integrated circuits this was due in part to the use of a wider bias range, the addition of inherent parasitic elements and the occurrence of multi dimensional effects in smaller devices. Since powerful computing aids became available at the same time, complicated situations in complex configurations could be analyzed by useful numerical techniques. Despite the resulting progress in device optimization, the above approach fails to provide a required compact set of device design and process control rules and a compact circuit model for the analysis of large-scale electronic designs. This book therefore takes up the original thread to some extent. Taking into account new physical effects and introducing useful but correct simplifying assumptions, the previous concepts of analytic device models have been extended to describe the characteristics of modern integrated circuit devices. This has been made possible by making extensive use of exact numerical results to gain insight into complicated situations of transistor operation.

This book teaches the principles of physical design, layout, and simulation of CMOS integrated circuits. It is written around a very powerful CAD program called Microwind that is available on the accompanying CD-ROM. Featuring a friendly interface, Microwind is both educational and useful for designing CMOS chips.

Most of the recent texts on compact modeling are limited to a particular class of semiconductor devices and do not provide comprehensive coverage of the field. Having a single comprehensive reference for the compact models of most commonly used semiconductor devices (both active and passive) represents a significant advantage for the reader. Indeed, several kinds of semiconductor devices are routinely encountered in a single IC design or in a single modeling support group. Compact Modeling includes mostly the material that after several years of IC design applications has been found both theoretically sound and practically significant. Assigning the individual chapters to the groups responsible for the definitive work on the subject assures the highest possible degree of expertise on each of the covered models.

Praise for CMOS: Circuit Design, Layout, and Simulation Revised Second Edition from the Technical Reviewers "A refreshing industrial flavor. Design concepts are presented as they are needed for 'just-in-time' learning. Simulating and designing circuits using SPICE is emphasized with literally hundreds of examples. Very few textbooks contain as much detail as this one. Highly

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recommended!" --Paul M. Furth, New Mexico State University "This book builds a solid knowledge of CMOS circuit design from the ground up. With coverage of process integration, layout, analog and digital models, noise mechanisms, memory circuits, references, amplifiers, PLLs/DLLs, dynamic circuits, and data converters, the text is an excellent reference for both experienced and novice designers alike." --Tyler J. Gomm, Design Engineer, Micron Technology, Inc. "The Second Edition builds upon the success of the first with new chapters that cover additional material such as oversampled converters and non-volatile memories. This is becoming the de facto standard textbook to have on every analog and mixed-signal designer's bookshelf." --Joe Walsh, Design Engineer, AMI Semiconductor CMOS circuits from design to implementation CMOS: Circuit Design, Layout, and Simulation, Revised Second Edition covers the practical design of both analog and digital integrated circuits, offering a vital, contemporary view of a wide range of analog/digital circuit blocks, the BSIM model, data converter architectures, and much more. This edition takes a two-path approach to the topics: design techniques are developed for both long- and short-channel CMOS technologies and then compared. The results are multidimensional explanations that allow readers to gain deep insight into the design process. Features include: Updated materials to reflect CMOS technology's movement into nanometer sizes Discussions on phase- and delay-locked loops, mixed-signal circuits, data converters, and circuit noise More than 1,000 figures, 200 examples, and over 500 end-of-chapter problems In-depth coverage of both analog and digital circuit-level design techniques Real-world process parameters and design rules The book's Web site, CMOSedu.com, provides: solutions to the book's problems; additional homework problems without solutions; SPICE simulation examples using HSPICE, LTspice, and WinSpice; layout tools and examples for actually fabricating a chip; and videos to aid learning

Responding to recent developments and a growing VLSI circuit manufacturing market, Technology Computer Aided Design: Simulation for VLSI MOSFET examines advanced MOSFET processes and devices through TCAD numerical simulations. The book provides a balanced summary of TCAD and MOSFET basic concepts, equations, physics, and new technologies related to TCAD and MOSFET. A firm grasp of these concepts allows for the design of better models, thus streamlining the design process, saving time and money. This book places emphasis on the importance of modeling and simulations of VLSI MOS transistors and TCAD software. Providing background concepts involved in the TCAD simulation of MOSFET devices, it presents concepts in a simplified manner, frequently using comparisons to everyday-life experiences. The book then explains concepts in depth, with required mathematics and program code. This book also details the classical semiconductor physics for understanding the principle of operations for VLSI MOS transistors, illustrates recent developments in the area of MOSFET and other electronic devices, and analyzes the evolution of the role of modeling and simulation of MOSFET. It also provides exposure to the two most commercially popular TCAD simulation tools Silvaco and Sentaurus. • Emphasizes the need for TCAD simulation to be included within VLSI design flow for nano-scale integrated circuits • Introduces the advantages of TCAD simulations for device and process technology characterization • Presents the fundamental physics and mathematics incorporated in the TCAD tools • Includes popular commercial TCAD simulation tools (Silvaco and Sentaurus) • Provides characterization of performances of VLSI

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MOSFETs through TCAD tools • Offers familiarization to compact modeling for VLSI circuit simulation R&D cost and time for electronic product development is drastically reduced by taking advantage of TCAD tools, making it indispensable for modern VLSI device technologies. They provide a means to characterize the MOS transistors and improve the VLSI circuit simulation procedure. The comprehensive information and systematic approach to design, characterization, fabrication, and computation of VLSI MOS transistor through TCAD tools presented in this book provides a thorough foundation for the development of models that simplify the design verification process and make it cost effective.

This book presents the art of advanced MOSFET modeling for integrated circuit simulation and design. It provides the essential mathematical and physical analyses of all the electrical, mechanical and thermal effects in MOS transistors relevant to the operation of integrated circuits. Particular emphasis is placed on how the BSIM model evolved into the first ever industry standard SPICE MOSFET model for circuit simulation and CMOS technology development. The discussion covers the theory and methodology of how a MOSFET model, or semiconductor device models in general, can be implemented to be robust and efficient, turning device physics theory into a production-worthy SPICE simulation model. Special attention is paid to MOSFET characterization and model parameter extraction methodologies, making the book particularly useful for those interested or already engaged in work in the areas of semiconductor devices, compact modeling for SPICE simulation, and integrated circuit design. This book facilitates the VLSI-interested individuals with not only in-depth knowledge, but also the broad aspects of it by explaining its applications in different fields, including image processing and biomedical. The deep understanding of basic concepts gives you the power to develop a new application aspect, which is very well taken care of in this book by using simple language in explaining the concepts. In the VLSI world, the importance of hardware description languages cannot be ignored, as the designing of such dense and complex circuits is not possible without them. Both Verilog and VHDL languages are used here for designing. The current needs of high-performance integrated circuits (ICs) including low power devices and new emerging materials, which can play a very important role in achieving new functionalities, are the most interesting part of the book. The testing of VLSI circuits becomes more crucial than the designing of the circuits in this nanometer technology era. The role of fault simulation algorithms is very well explained, and its implementation using Verilog is the key aspect of this book. This book is well organized into 20 chapters. Chapter 1 emphasizes on uses of FPGA on various image processing and biomedical applications. Then, the descriptions enlighten the basic understanding of digital design from the perspective of HDL in Chapters 2–5. The performance enhancement with alternate material or geometry for silicon-based FET designs is focused in Chapters 6 and 7. Chapters 8 and 9 describe the study of bimolecular interactions with biosensing FETs. Chapters 10–13 deal with advanced FET structures available in various shapes, materials such as nanowire, HFET, and their comparison in terms of device performance metrics calculation. Chapters 14–18 describe different application-specific VLSI design techniques and challenges for analog and digital circuit designs. Chapter 19 explains the VLSI testability issues with the description of simulation and its categorization into logic and fault simulation for test pattern generation using Verilog HDL. Chapter 20 deals with a secured VLSI design with hardware obfuscation

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by hiding the IC's structure and function, which makes it much more difficult to reverse engineer.

Continuous efforts to develop new semiconductor devices enable device manufacturers to make significant improvements in the information technology sector. Bipolar transistors and MOSFETS are two special electronic device components that are used to construct very large scale integrated (VLSI) circuits, allowing engineers to create powerful machines that are power efficient. VLSI device characterization depends largely on semiconductor device modeling which is based on physical and electronic principles. Bipolar transistor and MOSFET device models is a textbook that describes basic functions and characterization models of these two types of transistors. Readers will learn about the processes employed to derive these models which will help them understand the modeling process. Chapters in this text cover the fundamentals of semiconductor devices, the pn junction, high and low injection region models for bipolar transistors, and different MOSFET models such as channel doping models and gated SOI models. Key features of this book include: - step by step, easy to understand presentation of model information on innovative semiconductor devices - an overview of model derivation, assumptions, approximations and limitations - novel experimental information on semiconductor parameters such as gate fringe capacitance, silicided source/drain resistance, and threshold voltage shift Bipolar transistor and MOSFET device models is an essential learning resource for advanced students and professional engineers involved in semiconductor device modeling and fabrication divisions.

Technology computer-aided design, or TCAD, is critical to today's semiconductor technology and anybody working in this industry needs to know something about TCAD. This book is about how to use computer software to manufacture and test virtually semiconductor devices in 3D. It brings to life the topic of semiconductor device physics, with a hands-on, tutorial approach that de-emphasizes abstract physics and equations and emphasizes real practice and extensive illustrations. Coverage includes a comprehensive library of devices, representing the state of the art technology, such as SuperJunction LDMOS, GaN LED devices, etc.

The "Fifth International Conference on Simulation of Semiconductor Devices and Processes" (SISDEP 93) continues a series of conferences which was initiated in 1984 by K. Board and D. R. J. Owen at the University College of Wales, Swansea, where it took place a second time in 1986. Its organization was succeeded by G. Baccarani and M. Rudan at the University of Bologna in 1988, and W. Fichtner and D. Aemmer at the Federal Institute of Technology in Zurich in 1991. This year the conference is held at the Technical University of Vienna, Austria, September 7 - 9, 1993. This conference shall provide an international forum for the presentation of out standing research and development results in the area of numerical process and de vice simulation. The miniaturization of today's semiconductor devices, the usage of new materials and advanced process steps in the development of new semiconduc tor technologies suggests the design of new computer programs. This trend towards more complex structures and increasingly sophisticated processes demands advanced simulators, such as fully three-dimensional tools for almost arbitrarily complicated geometries. With

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the increasing need for better models and improved understanding of physical effects, the Conference on Simulation of Semiconductor Devices and Processes brings together the simulation community and the process- and device engineers who need reliable numerical simulation tools for characterization, prediction, and development.

Metal Oxide Semiconductor (MOS) transistors are the basic building block of MOS integrated circuits (IC). Very Large Scale Integrated (VLSI) circuits using MOS technology have emerged as the dominant technology in the semiconductor industry. Over the past decade, the complexity of MOS IC's has increased at an astonishing rate. This is realized mainly through the reduction of MOS transistor dimensions in addition to the improvements in processing. Today VLSI circuits with over 3 million transistors on a chip, with effective or electrical channel lengths of 0.5 microns, are in volume production. Designing such complex chips is virtually impossible without simulation tools which help to predict circuit behavior before actual circuits are fabricated. However, the utility of simulators as a tool for the design and analysis of circuits depends on the adequacy of the device models used in the simulator. This problem is further aggravated by the technology trend towards smaller and smaller device dimensions which increases the complexity of the models. There is extensive literature available on modeling these short channel devices. However, there is a lot of confusion too. Often it is not clear what model to use and which model parameter values are important and how to determine them. After working over 15 years in the field of semiconductor device modeling, I have felt the need for a book which can fill the gap between the theory and the practice of MOS transistor modeling. This book is an attempt in that direction.

Discover a fresh approach to efficient and insight-driven analog integrated circuit design in nanoscale-CMOS with this hands-on guide. Expert authors present a sizing methodology that employs SPICE-generated lookup tables, enabling close agreement between hand analysis and simulation. This enables the exploration of analog circuit tradeoffs using the g_m/I_D ratio as a central variable in script-based design flows, and eliminates time-consuming iterations in a circuit simulator. Supported by downloadable MATLAB code, and including over forty detailed worked examples, this book will provide professional analog circuit designers, researchers, and graduate students with the theoretical know-how and practical tools needed to acquire a systematic and re-use oriented design style for analog integrated circuits in modern CMOS.

Compact Models for Integrated Circuit Design: Conventional Transistors and Beyond provides a modern treatise on compact models for circuit computer-aided design (CAD). Written by an author with more than 25 years of industry experience in semiconductor processes, devices, and circuit CAD, and more than 10 years of academic experience in teaching compact modeling courses, this first-of-its-kind book on compact SPICE models for very-large-scale-integrated (VLSI) chip design offers a balanced presentation of compact modeling crucial for addressing current modeling

challenges and understanding new models for emerging devices. Starting from basic semiconductor physics and covering state-of-the-art device regimes from conventional micron to nanometer, this text: Presents industry standard models for bipolar-junction transistors (BJTs), metal-oxide-semiconductor (MOS) field-effect-transistors (FETs), FinFETs, and tunnel field-effect transistors (TFETs), along with statistical MOS models Discusses the major issue of process variability, which severely impacts device and circuit performance in advanced technologies and requires statistical compact models Promotes further research of the evolution and development of compact models for VLSI circuit design and analysis Supplies fundamental and practical knowledge necessary for efficient integrated circuit (IC) design using nanoscale devices Includes exercise problems at the end of each chapter and extensive references at the end of the book Compact Models for Integrated Circuit Design: Conventional Transistors and Beyond is intended for senior undergraduate and graduate courses in electrical and electronics engineering as well as for researchers and practitioners working in the area of electron devices. However, even those unfamiliar with semiconductor physics gain a solid grasp of compact modeling concepts from this book. The Open Access version of this book, available at <https://doi.org/10.1201/b19117>, has been made available under a Creative Commons Attribution-Non Commercial-No Derivatives 4.0 license.

This volume provides a timely description of the latest compact MOS transistor models for circuit simulation. The first generation BSIM3 and BSIM4 models that have dominated circuit simulation in the last decade are no longer capable of characterizing all the important features of modern sub-100nm MOS transistors. This book discusses the second generation MOS transistor models that are now in urgent demand and being brought into the initial phase of manufacturing applications. It considers how the models are to include the complete drift-diffusion theory using the surface potential variable in the MOS transistor channel in order to give one characterization equation.

Improve your circuit-design potential with this expert guide to the devices and technology used in mixed analog-digital VLSI chips for such high-volume applications as hard-disk drives, wireless telephones, and consumer electronics. The book provides you with a critical understanding of device models, fabrication technology, and layout as they apply to mixed analog-digital circuits. You will learn about the many device-modeling requirements for analog work, as well as the pitfalls in models used today for computer simulators such as Spice. Also included is information on fabrication technologies developed specifically for mixed-signal VLSI chips, plus guidance on the layout of mixed analog-digital chips for a high degree of analog-device matching and minimum digital-to-analog interference. This reference book features an intuitive introduction to MOSFET operation that will enable you to view with insight any MOSFET model ? besides thorough discussions on valuable large-signal and small-signal models. Filled with practical information, this first-of-its-

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kind book will help you grasp the nuances of mixed-signal VLSI-device models and layout that are crucial to the design of high-performance chips.

The essentials of analog circuit design with a unique all-region MOSFET modeling approach.

Bridges the gap between device modelling and analog circuit design. Includes dedicated software enabling actual circuit design. Covers the three significant models: BSIM3, Model 9 &, and EKV. Presents practical guidance on device development and circuit implementation. The authors offer a combination of extensive academic and industrial experience.

A reprint of the classic text, this book popularized compact modeling of electronic and semiconductor devices and components for college and graduate-school classrooms, and manufacturing engineering, over a decade ago. The first comprehensive book on MOS transistor compact modeling, it was the most cited among similar books in the area and remains the most frequently cited today. The coverage is device-physics based and continues to be relevant to the latest advances in MOS transistor modeling. This is also the only book that discusses in detail how to measure device model parameters required for circuit simulations. The book deals with the MOS Field Effect Transistor (MOSFET) models that are derived from basic semiconductor theory. Various models are developed, ranging from simple to more sophisticated models that take into account new physical effects observed in submicron transistors used in today's (1993) MOS VLSI technology. The assumptions used to arrive at the models are emphasized so that the accuracy of the models in describing the device characteristics are clearly understood. Due to the importance of designing reliable circuits, device reliability models are also covered. Understanding these models is essential when designing circuits for state-of-the-art MOS ICs.

This book is the first to explain FinFET modeling for IC simulation and the industry standard – BSIM-CMG - describing the rush in demand for advancing the technology from planar to 3D architecture, as now enabled by the approved industry standard. The book gives a strong foundation on the physics and operation of FinFET, details aspects of the BSIM-CMG model such as surface potential, charge and current calculations, and includes a dedicated chapter on parameter extraction procedures, providing a step-by-step approach for the efficient extraction of model parameters. With this book you will learn: Why you should use FinFET The physics and operation of FinFET Details of the FinFET standard model (BSIM-CMG) Parameter extraction in BSIM-CMG FinFET circuit design and simulation Authored by the lead inventor and developer of FinFET, and developers of the BSIM-CM standard model, providing an experts' insight into the specifications of the standard The first book on the industry-standard FinFET model - BSIM-CMG

Modern, large-scale analog integrated circuits (ICs) are essentially composed of metal-oxide semiconductor (MOS) transistors and their interconnections. As technology scales down to deep sub-micron dimensions and supply voltage decreases to reduce power consumption, these complex analog circuits are even more dependent on the exact behavior of each transistor. High-performance analog circuit design requires a very detailed model of the transistor, describing accurately its static and dynamic behaviors, its noise and matching limitations and its temperature variations. The charge-based EKV (Enz-Krummenacher-Vittoz) MOS transistor model for IC design has been developed to provide a clear understanding of the device properties, without the use of complicated equations. All the static, dynamic, noise, non-quasi-static models are completely described in terms of the inversion charge at the source and at the drain taking advantage of the symmetry of the device. Thanks to its hierarchical structure, the model offers several coherent description levels, from basic hand calculation equations to complete computer simulation model. It is also compact, with a minimum number of process-dependant device parameters. Written by its

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developers, this book provides a comprehensive treatment of the EKV charge-based model of the MOS transistor for the design and simulation of low-power analog and RF ICs. Clearly split into three parts, the authors systematically examine: the basic long-channel intrinsic charge-based model, including all the fundamental aspects of the EKV MOST model such as the basic large-signal static model, the noise model, and a discussion of temperature effects and matching properties; the extended charge-based model, presenting important information for understanding the operation of deep-submicron devices; the high-frequency model, setting out a complete MOS transistor model required for designing RF CMOS integrated circuits. Practising engineers and circuit designers in the semiconductor device and electronics systems industry will find this book a valuable guide to the modelling of MOS transistors for integrated circuits. It is also a useful reference for advanced students in electrical and computer engineering.

Reliability concerns and the limitations of process technology can sometimes restrict the innovation process involved in designing nano-scale analog circuits. The success of nano-scale analog circuit design requires repeat experimentation, correct analysis of the device physics, process technology, and adequate use of the knowledge database. Starting with the basics, *Nano-Scale CMOS Analog Circuits: Models and CAD Techniques for High-Level Design* introduces the essential fundamental concepts for designing analog circuits with optimal performances. This book explains the links between the physics and technology of scaled MOS transistors and the design and simulation of nano-scale analog circuits. It also explores the development of structured computer-aided design (CAD) techniques for architecture-level and circuit-level design of analog circuits. The book outlines the general trends of technology scaling with respect to device geometry, process parameters, and supply voltage. It describes models and optimization techniques, as well as the compact modeling of scaled MOS transistors for VLSI circuit simulation.

- Includes two learning-based methods: the artificial neural network (ANN) and the least-squares support vector machine (LS-SVM) method
- Provides case studies demonstrating the practical use of these two methods
- Explores circuit sizing and specification translation tasks
- Introduces the particle swarm optimization technique and provides examples of sizing analog circuits

Discusses the advanced effects of scaled MOS transistors like narrow width effects, and vertical and lateral channel engineering *Nano-Scale CMOS Analog Circuits: Models and CAD Techniques for High-Level Design* describes the models and CAD techniques, explores the physics of MOS transistors, and considers the design challenges involving statistical variations of process technology parameters and reliability constraints related to circuit design.

This book will help CMOS circuit designers make the best possible use of SPICE models, and will prepare them for new models that may soon be introduced. Introduces SPICE modeling and its use in CMOS circuit design. Presents the formalism of model building and the semiconductor physics of MOS structures. Covers each important SPICE model, showing how to choose the appropriate model. Discusses the popular HSPICE Level 28, as well as Levels 1-3, BSIM 1-3, and MOS Model 9. Presents techniques for accounting for systematic process variations. Describes new model candidates, including the Power-Lane Model, the PCIM Model, and the EKV Model. Includes extensive examples throughout. Practicing engineers and scientists in the semiconductor industry; engineering faculty and students. This is the first book dedicated to the next generation of MOSFET models. Addressed to circuit designers with an in-depth treatment that appeals to device specialists, the book presents a fresh view of compact modeling, having completely abandoned the regional modeling approach. Both an overview of the basic physics theory required to build compact MOSFET models and a unified treatment of inversion-charge and surface-potential models are provided. The needs of digital, analog and RF designers as regards the availability of simple equations for circuit designs are taken into account. Compact expressions for hand analysis or for automatic synthesis, valid in all operating

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regions, are presented throughout the book. All the main expressions for computer simulation used in the new generation compact models are derived. Since designers in advanced technologies are increasingly concerned with fluctuations, the modeling of fluctuations is strongly emphasized. A unified approach for both space (matching) and time (noise) fluctuations is introduced.

This new book, written by Andre Vladimirescu, who was instrumental in the development of SPICE at the University of California Berkeley, introduces computer simulation of electrical and electronics circuits based on the SPICE standard. Relying on the functionality first supported in SPICE2 that is now supported in all SPICE programs, this text is addressed to all users of electrical simulation. The approach to learning circuit simulation is to interpret simulation results in relation to electrical engineering fundamentals; the book asks the student to solve most circuit examples by hand before verifying the results with SPICE. Addressed to both the SPICE novice and the experienced user, the first six chapters provide the relevant information on SPICE functionality for the analysis of linear as well as nonlinear circuits. Each of these chapters starts out with a linear example accessible to any new user of SPICE and proceeds with nonlinear transistor circuits. The latter part of the book goes into more detail on such issues as functional and hierarchical models, distortion analysis, basic algorithms in SPICE and related options parameters, and, how to direct SPICE to find a solution when it does not converge to a solution. The approach emphasizes that SPICE is not a substitute for knowledge of circuit operation but a complement. The SPICE Book is different from previously published books in the approach of solving circuit problems with a computer. The solution to most circuit examples is sketched out by hand first and followed by a SPICE verification. For more complex circuits it is not feasible to find the solution by hand but the approach stresses the need for the SPICE user to understand the results. Readers gain a better comprehension of SPICE thanks to the importance placed on the relation between EE fundamentals and computer simulation. The tutorial approach advances from the hand solution of a circuit to SPICE verification and simulation results interpretation. This book teaches the approach to electrical circuit simulation rather than a specific simulation program. Examples are simulated alternatively with SPICE2, SPICE3 or PSPICE. Accurate descriptions, simulation rationale and cogent explanations make this an invaluable reference.

The aim of this book is to highlight the benefits of a higher interoperability between Technology Computer-Aided Design and Electronic Design Automation, focusing on specifically selected open source tools for compact modeling. Due to the tremendous developments in semiconductor technology in recent years, device level modelling and integrated circuit design have become intimately related. However, they have been traditionally disconnected up to the circuit level. This book consists of a set of extended user manuals guiding the reader from the usual software, from multidimensional numerical process and device simulations, through compact model development and its Verilog-A standardization to carefully selected IC designs for analog, radio frequency and digital applications. Bringing together contributions from academic and industrial researchers and engineers, the book forms a valuable reference for students and those working in the field.

Understand the theory, design and applications of the two principal candidates for the next mainstream semiconductor-industry device with this concise and clear guide to FD/UTB transistors. • Describes FD/SOI MOSFETs and 3-D FinFETs in detail • Covers short-channel effects, quantum-mechanical effects, applications of UTB devices to floating-body DRAM

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and conventional SRAM • Provides design criteria for nanoscale FinFET and nanoscale thin- and thick-BOX planar FD/SOI MOSFET to help reduce technology development time • Projects potential nanoscale UTB CMOS performances • Contains end-of-chapter exercises. For professional engineers in the CMOS IC field who need to know about optimal non-classical device design and integration, this is a must-have resource.

This volume features the refereed proceedings of the 17th International Workshop on Power and Timing Modeling, Optimization and Simulation. Papers cover high level design, low power design techniques, low power analog circuits, statistical static timing analysis, power modeling and optimization, low power routing optimization, security and asynchronous design, low power applications, modeling and optimization, and more.

Learn the basic properties and designs of modern VLSI devices, as well as the factors affecting performance, with this thoroughly updated second edition. The first edition has been widely adopted as a standard textbook in microelectronics in many major US universities and worldwide. The internationally renowned authors highlight the intricate interdependencies and subtle trade-offs between various practically important device parameters, and provide an in-depth discussion of device scaling and scaling limits of CMOS and bipolar devices. Equations and parameters provided are checked continuously against the reality of silicon data, making the book equally useful in practical transistor design and in the classroom. Every chapter has been updated to include the latest developments, such as MOSFET scale length theory, high-field transport model and SiGe-base bipolar devices.

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